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## **Terrestrial neutron effects on commercial SiC power MOSFETs**

*Tuesday 2 February 2021 18:00 (15 minutes)*

Accelerated terrestrial neutron irradiations were performed on commercial SiC power MOSFETs with planar, trench and double-trench architectures. Enhanced gate and drain leakage were observed in some devices which did not exhibit a destructive failure during the exposure. Failure cross-sections and FIT rates are discussed for the three architectures.

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